

General Description

The WSD2022DN33 is the highest performance trench Dual N-Channel MOSFET with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications .

The WSD2022DN33 meet the RoHS and Green Product requirement 100% E_{AS} guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% E_{AS} Guaranteed
- Green Device Available

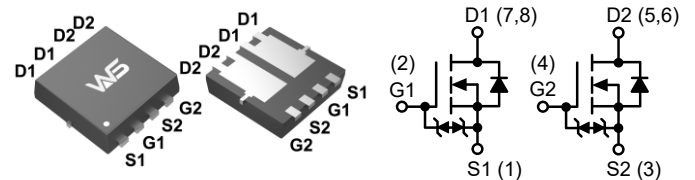
Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D
20V	16.2m Ω	22A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN3X3-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 8	
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ¹	22	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ¹	4.8	
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ¹	7.4	
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ¹	5.7	
I_{DM}	Pulsed Drain Current ²	24	
E_{AS}	Single Pulse Avalanche Energy ³	15	mJ
I_{AS}	Avalanche Current	16	A
$P_D@T_C=25^\circ C$	Power Dissipation ⁴	2.5	W
$P_D@T_A=25^\circ C$	Power Dissipation ⁴	1.6	
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	

Thermal Data

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient ¹	---	75	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case ¹	---	8.5	

Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.0332	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =8A	---	16.2	21	mΩ
		V _{GS} =2.5V, I _D =7A	---	19.4	25	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250μA	0.4	0.52	1.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.08	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =20V, V _{GS} =0V, T _J =25°C	---	---	1.0	μA
		V _{DS} =20V, V _{GS} =0V, T _J =55°C	---	---	5.0	
I _{GSS}	Gate-Source Leakage Current	V _{DS} =0V, V _{GS} =±8V	---	---	±10	μA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =6.5A	---	13	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f = 1.0MHz	---	2.2	3.0	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =10V, V _{GS} =4.5V, I _D =8A	---	13.8	17.94	nC
Q _{gs}	Gate-Source Charge		---	4.1	5.33	
Q _{gd}	Gate-Drain Charge		---	5.6	7.28	
T _{d(on)}	Turn-On Delay Time	V _{DD} =10V, V _{GEN} =5V, R _G =3Ω I _D =1A, R _L =1.5Ω	---	6.2	12.4	ns
T _r	Rise Time		---	12.7	25.4	
T _{d(off)}	Turn-Off Delay Time		---	51.7	103.4	
T _f	Fall Time		---	16	32	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f = 1.0MHz	---	1160	---	pF
C _{OSS}	Output Capacitance		---	104	---	
C _{rss}	Reverse Transfer Capacitance		---	29	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy ⁵	V _{DD} =25V, L=0.1mH, I _{AS} =7.5A	15	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	5	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	25	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =2A, T _J =25°C	---	---	1.0	V
t _{rr}	Reverse Recovery Time	I _F =7.5A, dI/dt=100A/μs, T _J =25°C	---	13	---	ns
Q _{rr}	Reverse Recovery Charge		---	3	---	nC

Note:

- The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, t_s≤10sec.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The E_{AS} data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=7.5A
- The power dissipation is limited by 150°C junction temperature.
- The Min. value is 100% E_{AS} tested guarantee.
- The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

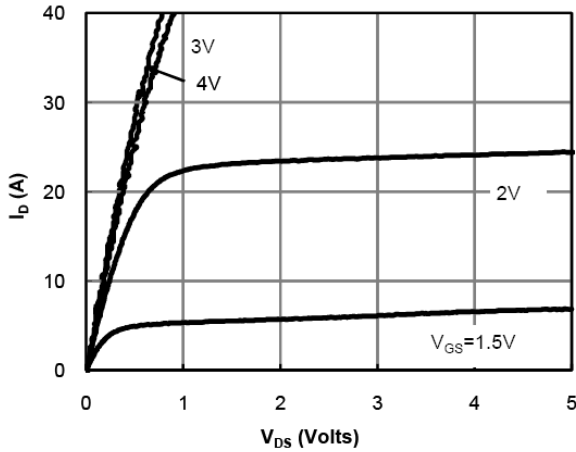


Fig 1: On-Region Characteristics

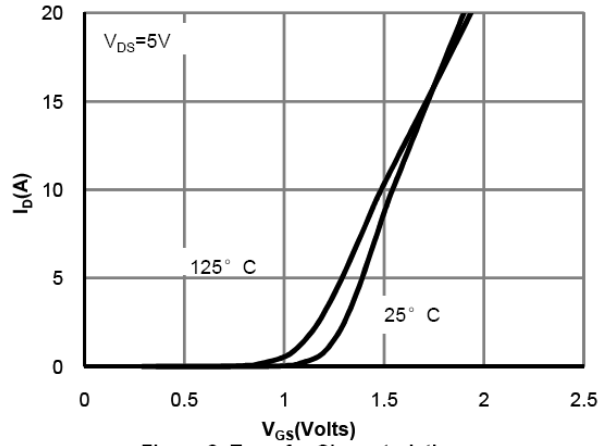


Figure 2: Transfer Characteristics

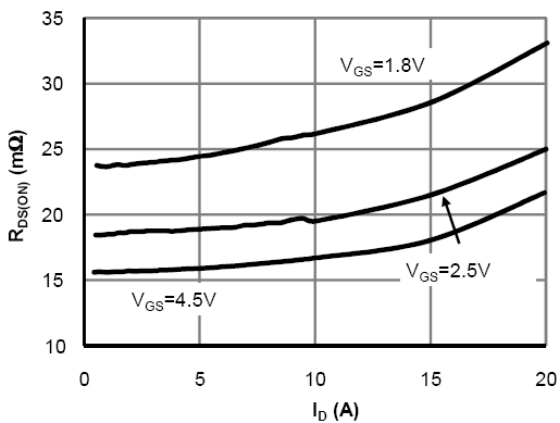


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

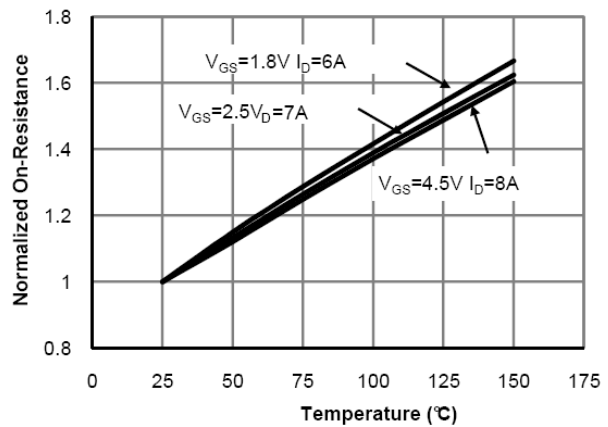


Figure 4: On-Resistance vs. Junction Temperature

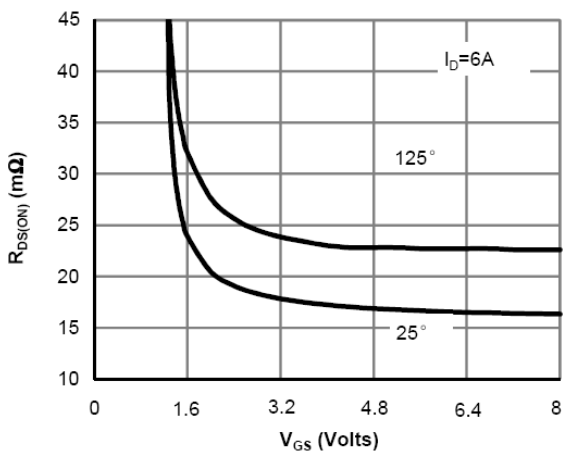


Figure 5: On-Resistance vs. Gate-Source Voltage

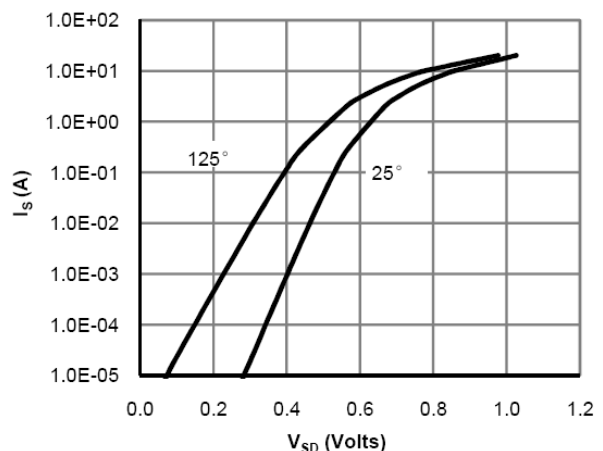


Figure 6: Body-Diode Characteristics

Typical Characteristics (Cont.)

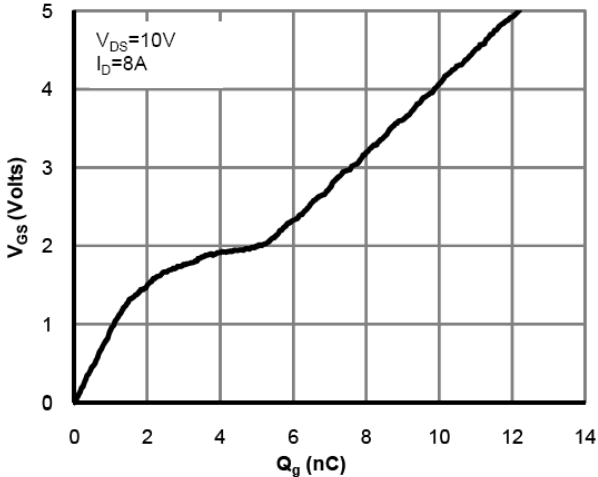


Figure 7: Gate-Charge Characteristics

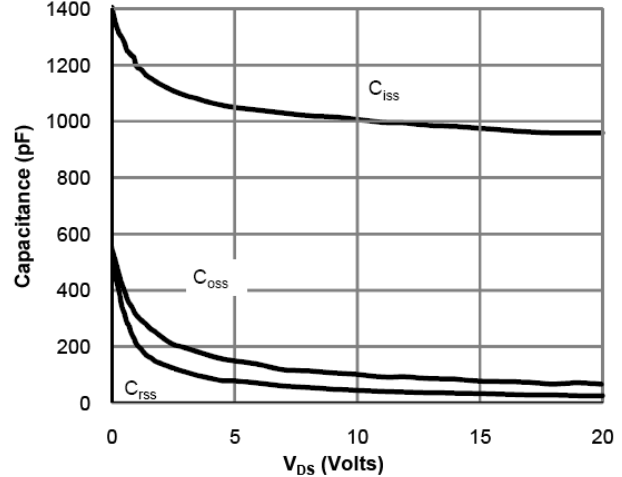


Figure 8: Capacitance Characteristics

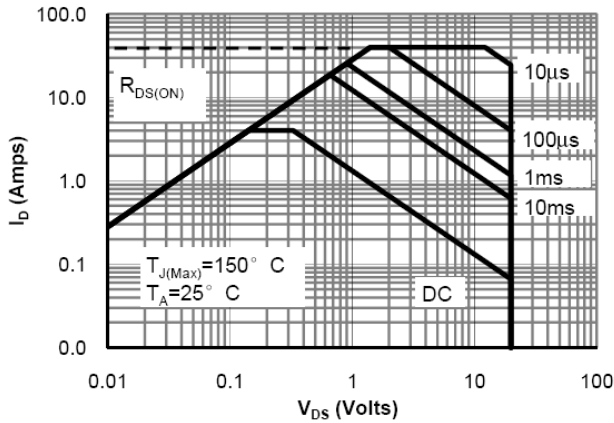


Figure 9: Maximum Forward Biased Safe Operating Area

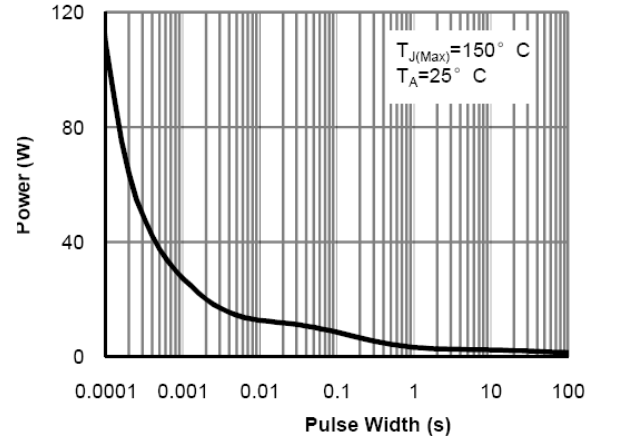


Figure 10: Single Pulse Power Rating Junction-to-Case

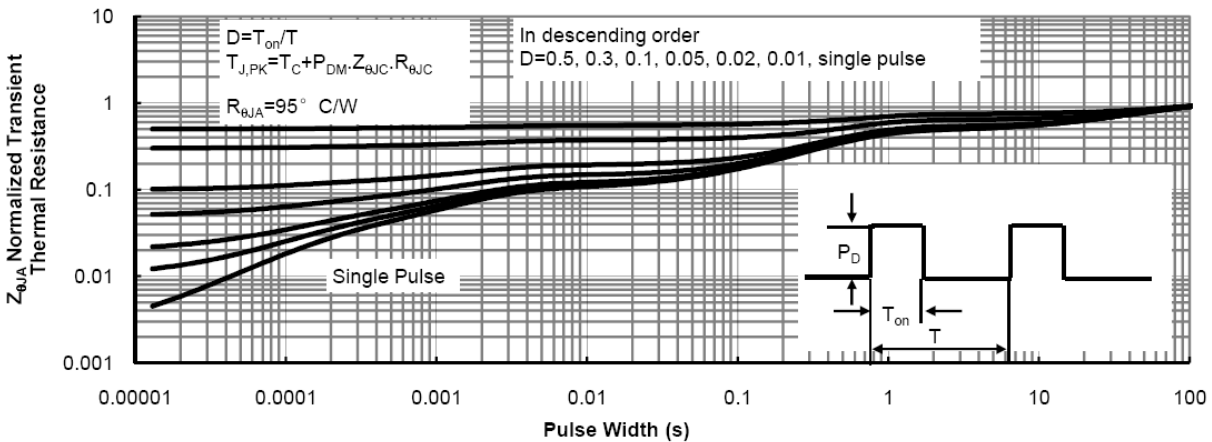
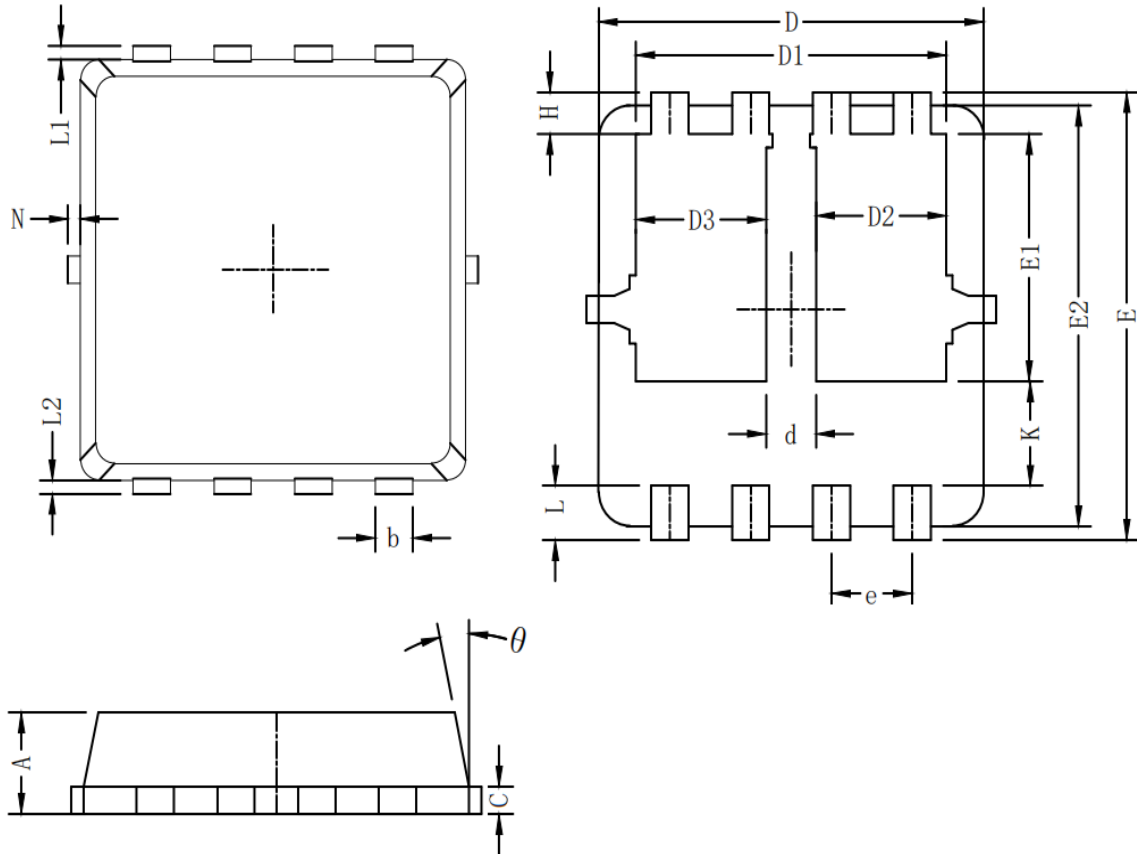


Figure 11: Normalized Maximum Transient Thermal Impedance

Packaging information


Symbol	Dim in mm		
	min	typ	max
A	0.6	0.75	0.9
b	0.2	0.3	0.4
C	0.15	0.2	0.25
D	3	3.1	3.2
D1	2.3	2.45	2.6
D2/D3	0.8	1	1.2
E	3.15	3.3	3.45
E1	1.43	1.73	1.93
E2	2.9	3.05	3.2
e	0.65BSC		
H	0.2	0.35	0.5
K	0.57	0.77	0.87
L	0.3	0.4	0.5
L1/L2	0.1REF		
θ	8°	10°	13°
N	0		0.15
d	0.3	0.4	0.5

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